

L Number	Hits	Search Text	DB	Time stamp
1	108151	((257/.cccls. 438/.cccls. 427/.cccls.) and @PY>=2001	USPAT; US-PGPUB; EPO; JPO	2004/10/29 10:31
2	6413	((257/.cccls. 438/.cccls. 427/.cccls.) and @PY>=2001) and (conduct\$3 metal\$3) near7 (sidewall\$1 wall\$1 side\$1) near3 (spacer\$1 coat\$3 flank\$3 cover\$3 protect\$3 lin\$3)	USPAT; US-PGPUB; EPO; JPO	2004/10/29 10:33
3	1247	((257/.cccls. 438/.cccls. 427/.cccls.) and @PY>=2001) and (conduct\$3 metal\$3) near7 (sidewall\$1 wall\$1 side\$1) near3 (spacer\$1 coat\$3 flank\$3 cover\$3 protect\$3 lin\$3) and (conduct\$3 metal\$3) same (barrier nitride\$1 titanium ti w tungsten tin wn) same (dielectric insulat\$3) same (planar planari\$6 flatten\$3 polish\$3 cmp) (((257/.cccls. 438/.cccls. 427/.cccls.) and @PY>=2001) and (conduct\$3 metal\$3) near7 (sidewall\$1 wall\$1 side\$1) near3 (spacer\$1 coat\$3 flank\$3 cover\$3 protect\$3 lin\$3)) and (conduct\$3 metal\$3) same (barrier nitride\$1 titanium ti w tungsten tin wn) same (dielectric insulat\$3) same (planar planari\$6 flatten\$3 polish\$3 cmp)) and (conduct\$3 metal\$3) near7 (dielectric insulat\$3) near5 ("over" "on")	USPAT; US-PGPUB; EPO; JPO	2004/10/29 10:37
4	578	((((257/.cccls. 438/.cccls. 427/.cccls.) and @PY>=2001) and (conduct\$3 metal\$3) near7 (sidewall\$1 wall\$1 side\$1) near3 (spacer\$1 coat\$3 flank\$3 cover\$3 protect\$3 lin\$3)) and (conduct\$3 metal\$3) same (barrier nitride\$1 titanium ti w tungsten tin wn) same (dielectric insulat\$3) same (planar planari\$6 flatten\$3 polish\$3 cmp)) and (conduct\$3 metal\$3) near7 (dielectric insulat\$3) near5 ("over" "on")) and (conduct\$3 metal\$3) near7 (dielectric insulat\$3) same gate\$1	USPAT; US-PGPUB; EPO; JPO	2004/10/29 11:02
5	310	((((((257/.cccls. 438/.cccls. 427/.cccls.) and @PY>=2001) and (conduct\$3 metal\$3) near7 (sidewall\$1 wall\$1 side\$1) near3 (spacer\$1 coat\$3 flank\$3 cover\$3 protect\$3 lin\$3)) and (conduct\$3 metal\$3) same (barrier nitride\$1 titanium ti w tungsten tin wn) same (dielectric insulat\$3) same (planar planari\$6 flatten\$3 polish\$3 cmp)) and (conduct\$3 metal\$3) near7 (dielectric insulat\$3) near5 ("over" "on")) and (conduct\$3 metal\$3) near7 (dielectric insulat\$3) same gate\$1	USPAT; US-PGPUB; EPO; JPO	2004/10/29 11:02